

AN 1989-246545 [34] WPIDS <<LOGINID::20090120>>

DNC C1989-110238 [21]

DNN N1989-187711 [21]

TI Backing plate for sputtering target - containing copper comprising zinc, manganese, antimony, beryllium, calcium, chromium tellurium, yttrium and/or niobium, etc.

DC M13; U11

IN ISHIKURA C

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CYC 1

PIA JP 01180976 A 19890718 (198934)* JA 3[3]

ADT JP 01180976 A JP 1988-4094 19880112

PRAI JP 1988-4094 19880112

AB JP 01180976 A UPAB: 20050429

Backing plate that constitutes sputtering targets, contains at least 99.7 weight% purity Cu, to which 100-3,000 weight ppm of at least one of Zn, Mn, Sb, Be, Ca, Cr, Te, Y, Nb, Mo, Ta, and Sn were added.

USE - For mounting Cu clad sputtering target by metal bonding, preventing thermal pressure bonding with Cu substrate of clad target, capable of separating target material easily after sputtering.